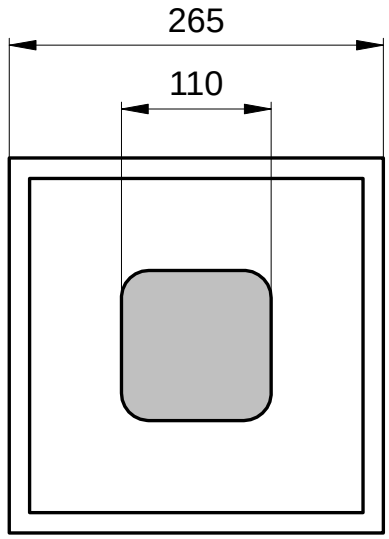
LED - CHIP ELC-650-23

preliminary

Color	Type	Technology	Electrodes
Red	Mesa	AlInGaP/GaAs	N (anode) up

Outline (typical dimensions in microns)



LED-12

thickness	260 µm
cathode	gold alloy, 1.5 µm
anode	gold alloy, 0.5 µm,

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 20 mA	V_F		2.1	2.4	V
Reverse voltage	I_R = 10 µA	V_R	5			V
Radiant power	I_F = 20 mA	Φ_e		1.1		mW
Luminous intensity	I_F = 20 mA	I_V		30		mcd
Radiant power*	I_F = 20 mA	Φ_e		2		mW
Luminous intensity*	I_F = 20 mA	I_V		60		mcd
Peak wavelength	I_F = 20 mA	λ_p		655		nm
Spectral bandwidth at 50%	I_F = 20 mA	$\Delta\lambda_{0.5}$		18		nm

*Measured on epoxy covered chip on TO-18 header

Labeling

Type	Lot N°	Φ_e (typ, min, max)	Quantity
ELC-650-23			

Packing

Chips on adhesive film with wire-bond side on top

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